

V <sub>RSM</sub> V <sub>RRM</sub>	I <sub>F</sub> RMS (maximum values for continuous operation) 100 A	
	I <sub>FAV</sub> (sin. 180; T <sub>case</sub> = . . . ) 50 A (105 °C)	50 A (95 °C)
	t <sub>tr</sub> = 200 ns	
V		
400	SKN 2 F 50/04 SKN 2 F 50/04 UNF	SKR 2 F 50/04 SKR 2 F 50/04 UNF
600	SKN 2 F 50/06 SKN 2 F 50/06 UNF	SKR 2 F 50/06 SKR 2 F 50/06 UNF
800	SKN 2 F 50/08 SKN 2 F 50/08 UNF	SKR 2 F 50/08 SKR 2 F 50/08 UNF
1000	SKN 2 F 50/10 SKN 2 F 50/10 UNF	SKR 2 F 50/10 SKR 2 F 50/10 UNF

## Fast Recovery Rectifier Diodes

SKN 2 F 50  
SKR 2 F 50



Symbol	Conditions	SKN 2 F 50	SKR 2 F 50	Units
I <sub>FAV</sub>	sin.180; (T <sub>case</sub> = . . . ); f = 5000 Hz sin.180/rec.120; T <sub>amb</sub> = 45 °C; K5 K3 K1,1	50 (105 °C) 12/11 18/17 33/31	50 (95 °C) 12/11 17/16 31/29	A A A A
I <sub>FSM</sub>	T <sub>vj</sub> = 25 °C; 10 ms T <sub>vj</sub> = 150 °C; 10 ms	1100 940	800 670	A A
i <sub>t</sub> <sup>2</sup>	T <sub>vj</sub> = 25 °C; 8,3 ... 10 ms T <sub>vj</sub> = 150 °C; 8,3 ... 10 ms	6000 4400	3200 2200	A <sup>2</sup> s A <sup>2</sup> s
Q <sub>tr</sub>	T <sub>vj</sub> = 130 °C; I <sub>f</sub> = 100 A;	3		μC
I <sub>RM</sub>	- dI <sub>f</sub> = 30 $\frac{A}{\mu s}$ ; V <sub>R</sub> = 30 V	10		A
I <sub>R</sub>	T <sub>vj</sub> = 25 °C; V <sub>R</sub> = V <sub>RRM</sub> T <sub>vj</sub> = 130 °C; V <sub>R</sub> = V <sub>RRM</sub>	0,4 50		mA mA
t <sub>tr</sub>	T <sub>vj</sub> = 25 °C T <sub>vj</sub> = 130 °C	I <sub>f</sub> = I <sub>R</sub> = 1 A	max. 200 typ. 400	ns ns
V <sub>f</sub>	T <sub>vj</sub> = 25 °C; I <sub>f</sub> = 50 A	max. 1,8		V
V <sub>(TO)</sub>	T <sub>vj</sub> = 150 °C	1,2		V
r <sub>T</sub>	T <sub>vj</sub> = 150 °C	4		mΩ
R <sub>tnjc</sub>		0,5	0,65	°C/W
R <sub>tnch</sub>		0,25		°C/W
T <sub>vj</sub>		- 40 ... + 150		°C
T <sub>stg</sub>		- 55 ... + 150		°C
M	SI units	2,5		Nm
a	US units	22		lb.in.
w	approx.	5 · 9,81		m/s <sup>2</sup>
Case		20		g
		E10		

### Features

- Small recovered charge
- Soft recovery
- Up to 1000 V reverse voltage
- Hermetic metal cases with glass insulators
- Threaded studs ISO M6 or 1/4-28 UNF
- **SKN:** anode to stud  
**SKR:** cathode to stud

### Typical Applications

- Inverse diodes for power transistors, GTO thyristors, asymmetric thyristors
- SMPS, inverters, choppers
- For severe ambient conditions

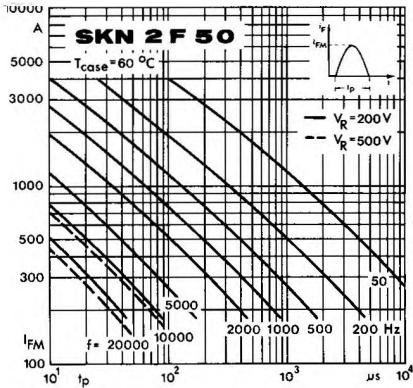


Fig. 1 a Rated sinusoidal peak forward current

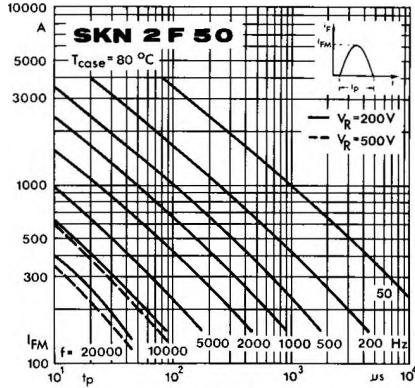


Fig. 1 b Rated sinusoidal peak forward current

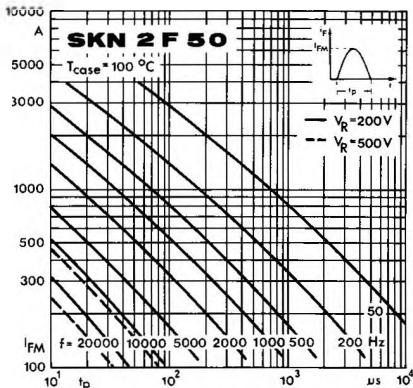


Fig. 1 c Rated sinusoidal peak forward current

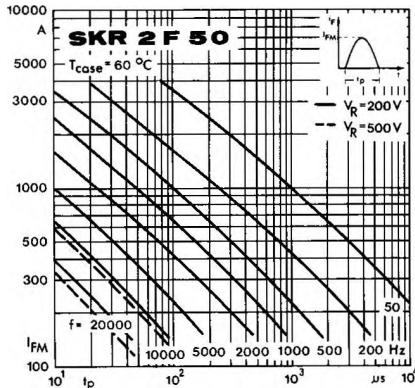


Fig. 1 d Rated sinusoidal peak forward current

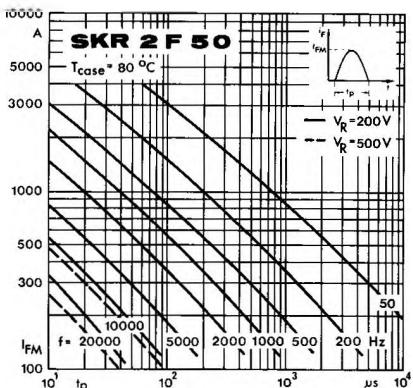


Fig. 1 e Rated sinusoidal peak forward current

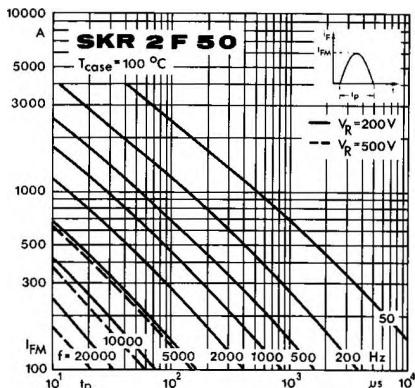


Fig. 1 f Rated sinusoidal peak forward current

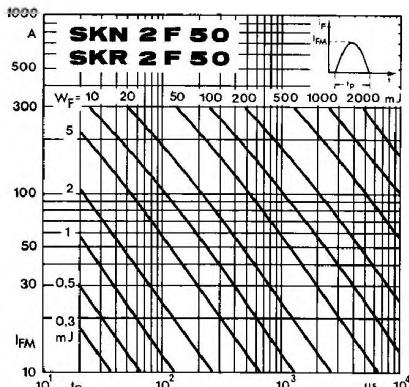


Fig. 2 Forward energy dissipation, sinusoidal

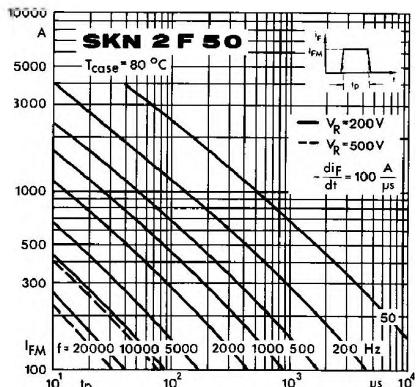


Fig. 3 b Rated rectangular peak forward current

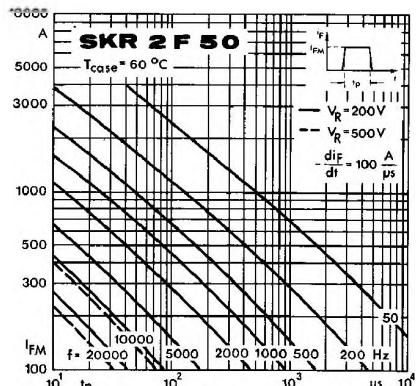


Fig. 3 d Rated rectangular peak forward current

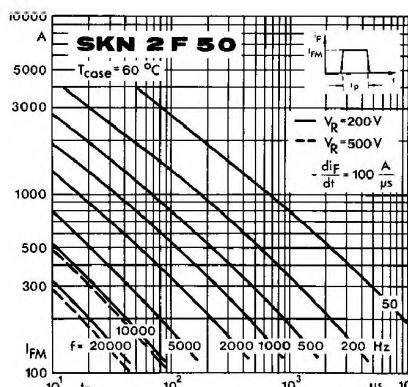


Fig. 3 a Rated rectangular peak forward current

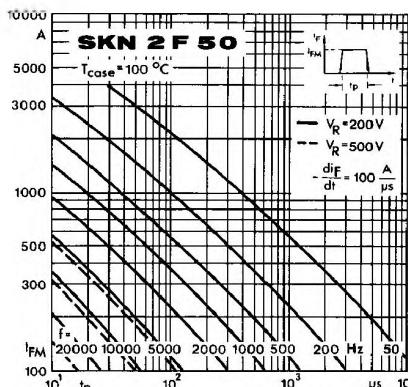


Fig. 3 c Rated rectangular peak forward current

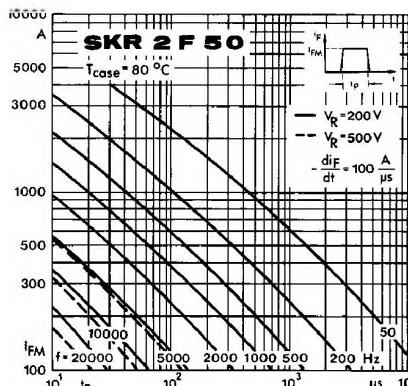


Fig. 3 e Rated rectangular peak forward current

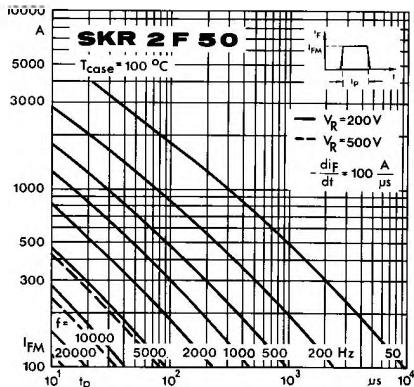


Fig. 3f Rated rectangular peak forward current

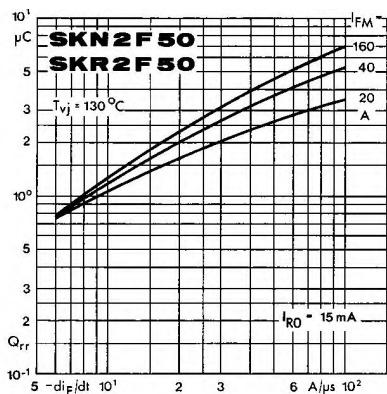


Fig. 5 Recovered charge

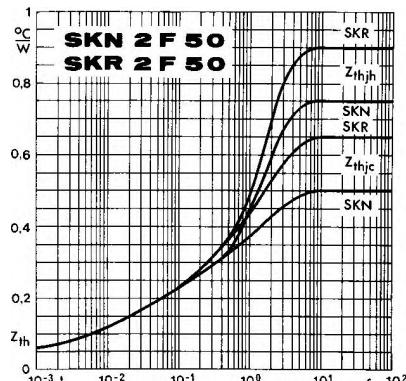


Fig. 7 Transient thermal impedance

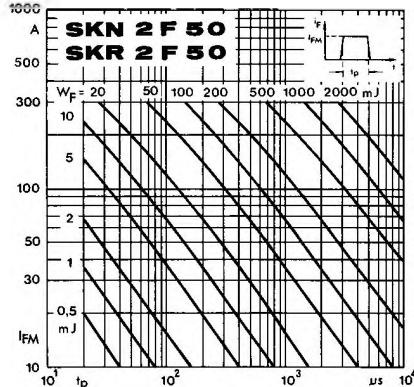


Fig. 4 Forward energy dissipation, rectangular

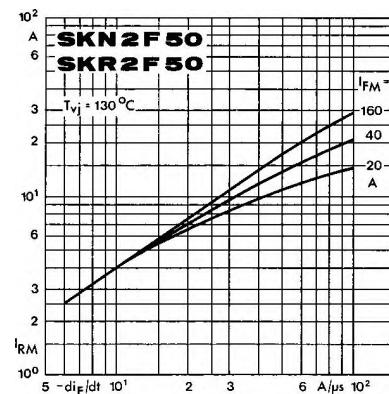


Fig. 6 Peak reverse recovery current

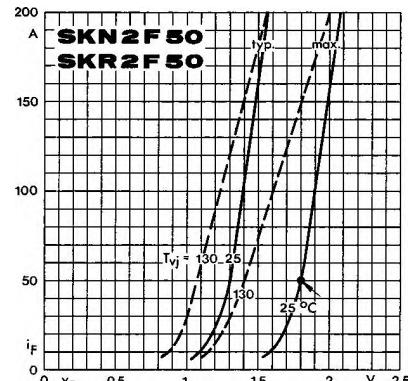


Fig. 8 Forward characteristics

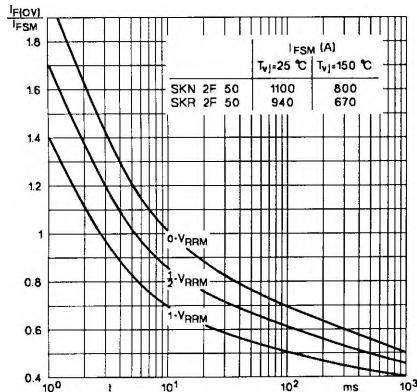
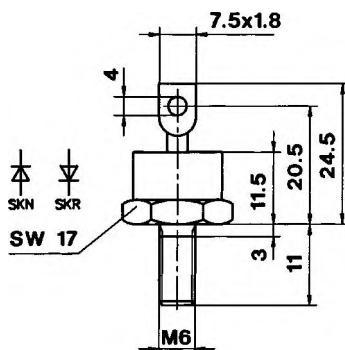


Fig. 9 Rated surge overload current

**SKN 2 F 50  
SKR 2 F 50**

Case E 10

IEC-Publ. 191-2: A 4 M

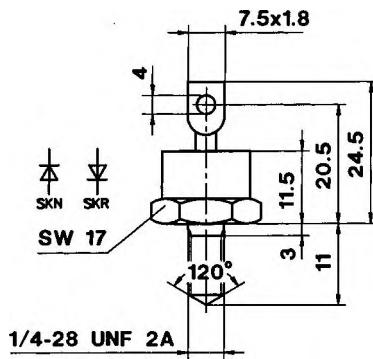


Dimensions in mm

**SKN 2 F 50 . . . UNF  
SKR 2 F 50 . . . UNF**

Case E 10 UNF

IEC-Publ. 191-2: A 4 U  
JEDEC: DO-203 AB (DO-5)



Dimensions in mm